



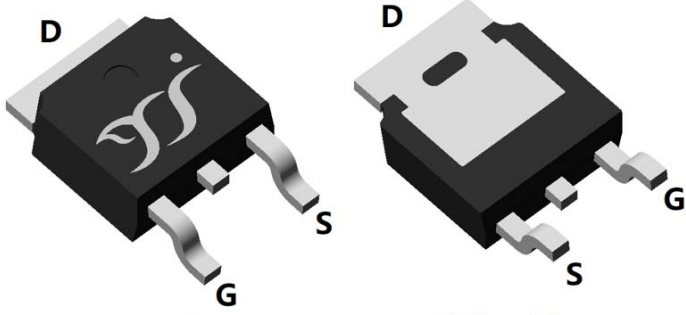
YJD45G10AQ

RoHS
COMPLIANT

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

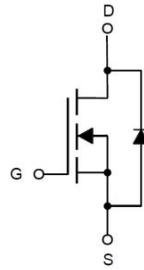
General Description



Top View

Bottom View

TO-252



Absolute Maximum Ratings

Parameter	Symbol	Limit
Drain-Source Voltage	V _{DS}	20 V
		10 V
		10 V
		10 V
Gate-Source Voltage	V _{GS}	10 V
		10 V
		10 V
		10 V
Drain Current (Continuous)	I _D	1.0 A
		1.0 A
		1.0 A
		1.0 A
Drain Current (Pulse)	I _{DM}	1.0 A
		1.0 A
		1.0 A
		1.0 A
Switching Frequency	f _{sw}	10 kHz
		10 kHz
		10 kHz
		10 kHz
Total Power Dissipation	P _D	1.0 W
		1.0 W
		1.0 W
		1.0 W
Storage Temperature	T _{stg}	-55 °C ~ 150 °C
		-55 °C ~ 150 °C
		-55 °C ~ 150 °C
		-55 °C ~ 150 °C



Thermal resistance

Parameter	Typ	Max	Unit

Ordering Information

PREFERRED P/N	PACKAGE	Material	MINIMUM PACK QUANTITY(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE

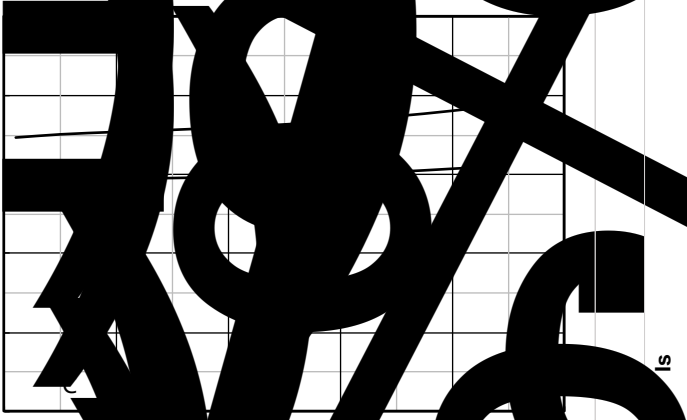
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Typical Electrical and Thermal Characteristics Diagrams

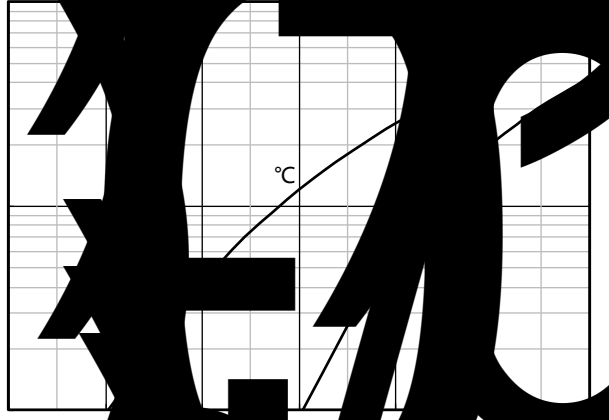


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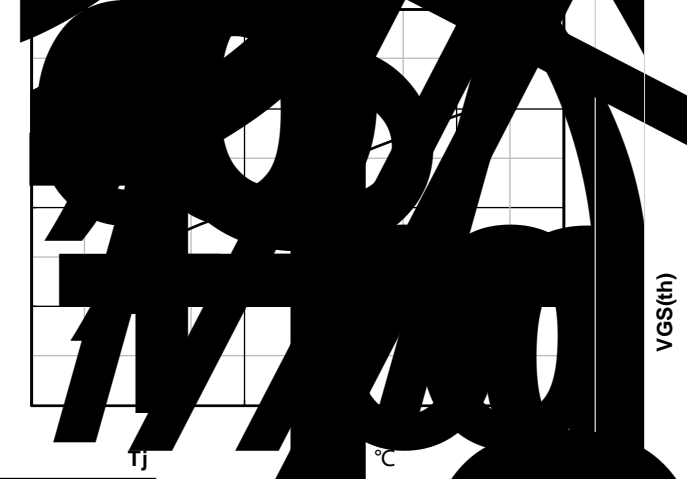
$R_{DS(on)}$



$^{\circ}C$



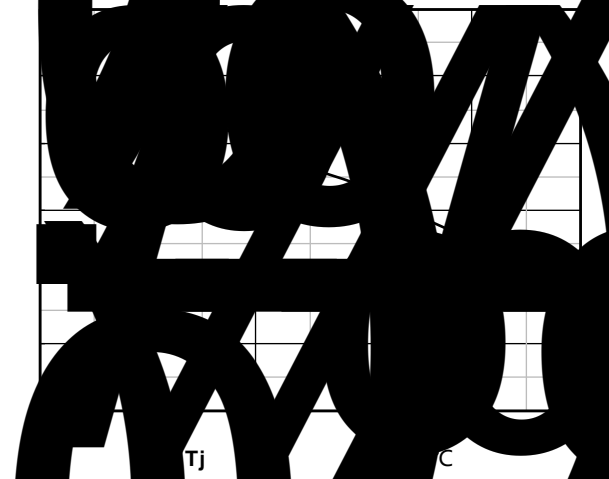
BV_{DSS}



T_j

$^{\circ}C$

$V_{GS(th)}$



T_j

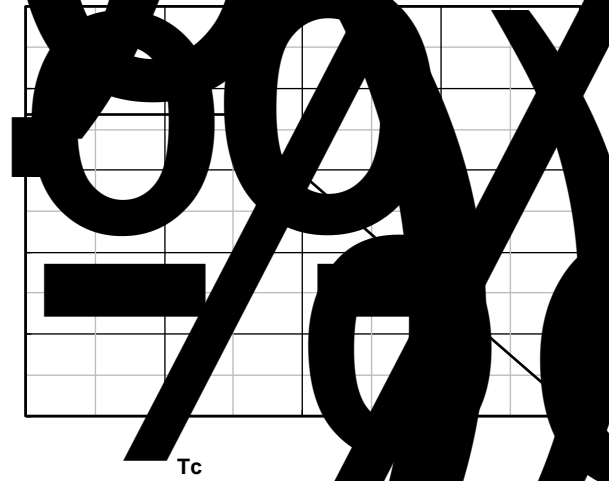
$^{\circ}C$

ID

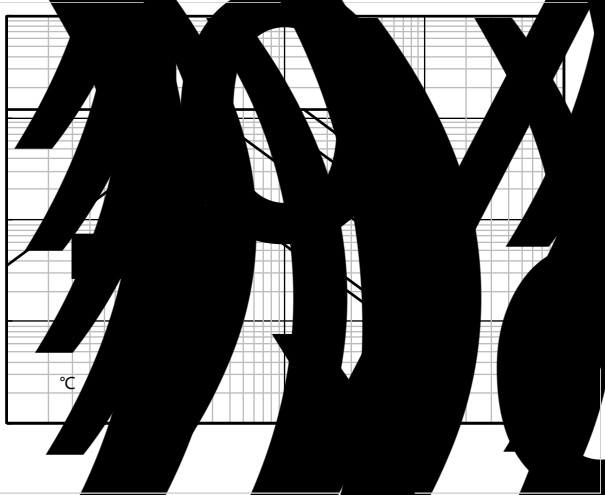
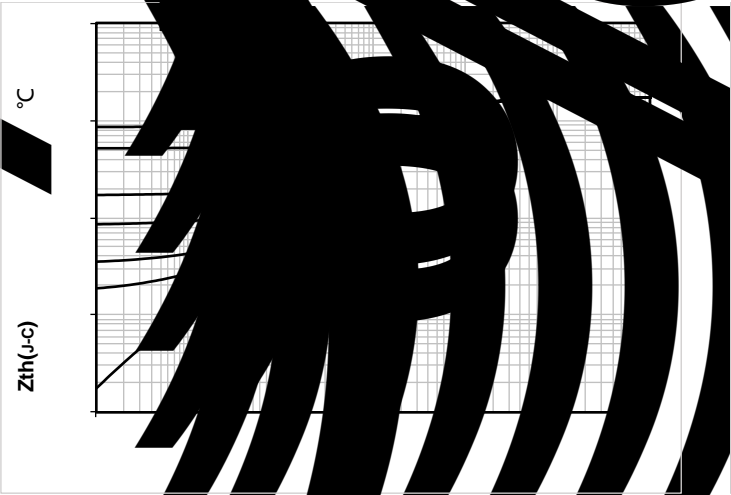
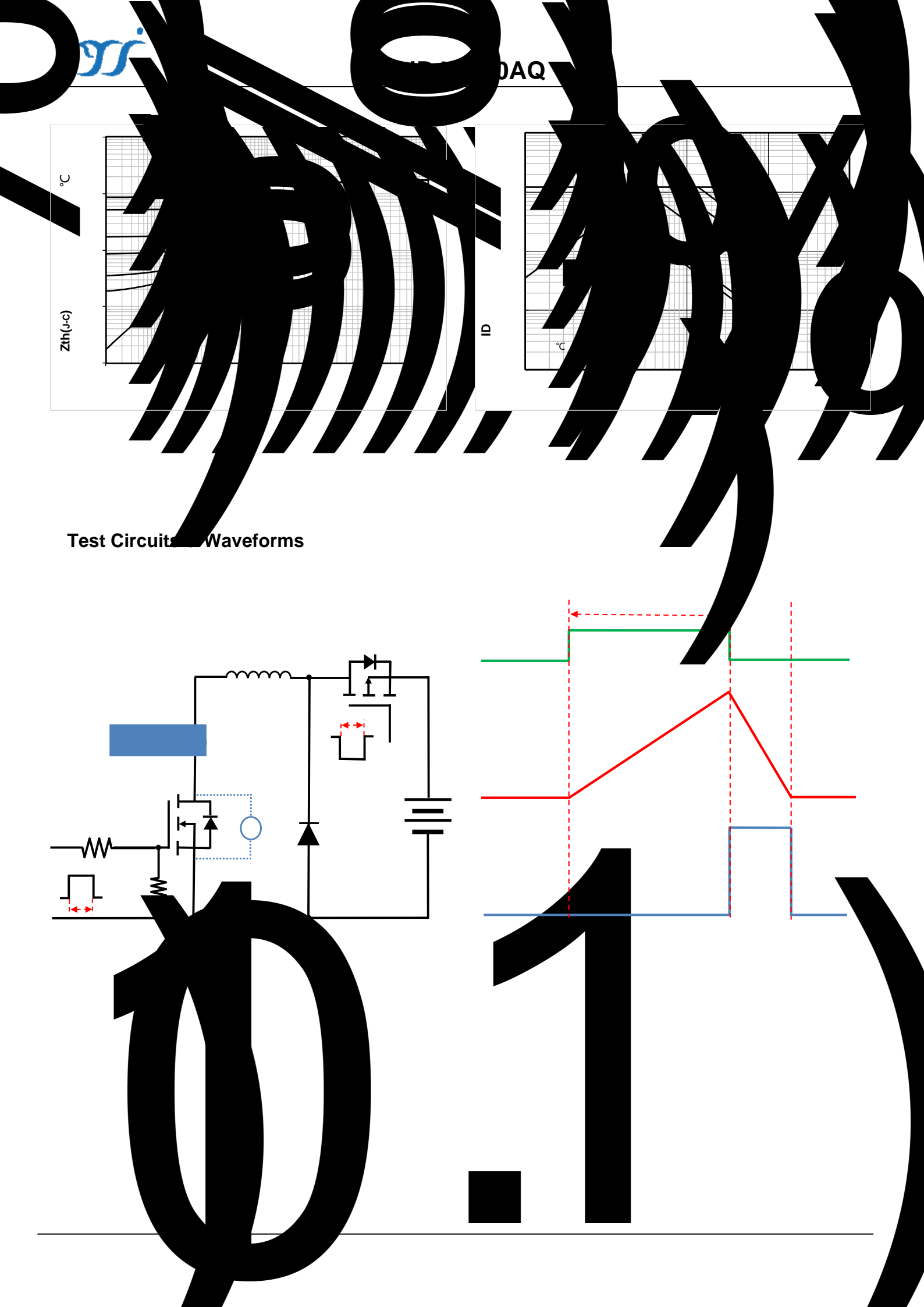


T_c

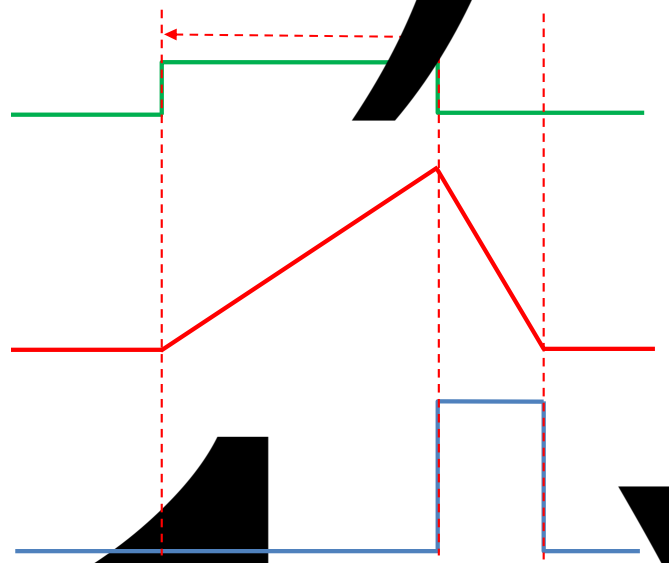
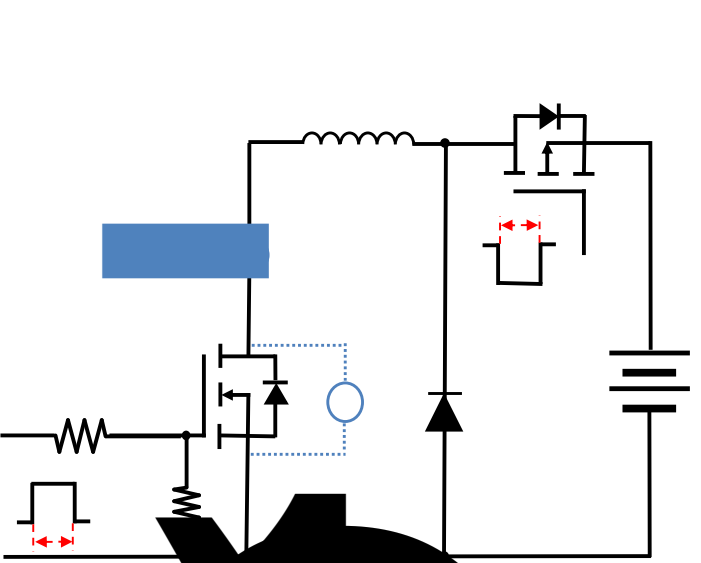
P_{tot}



T_c

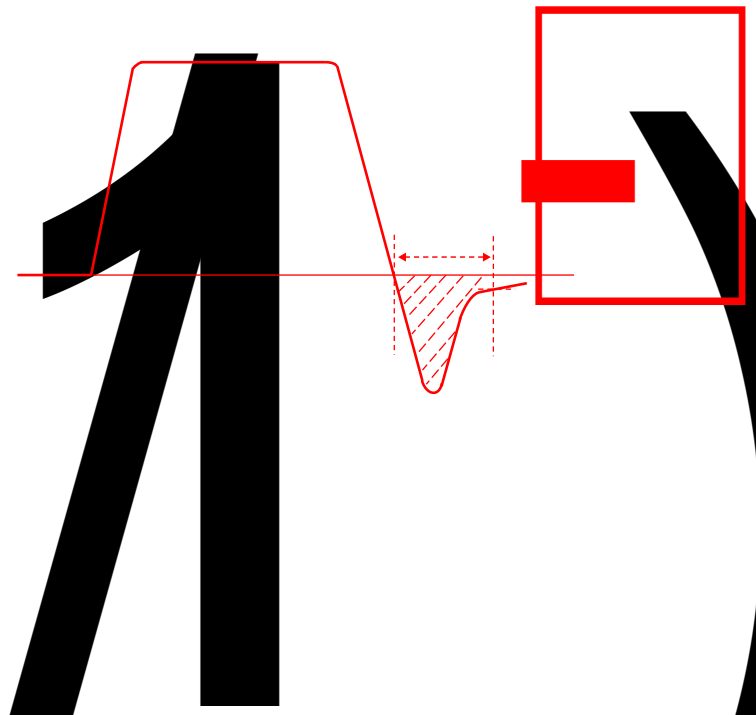
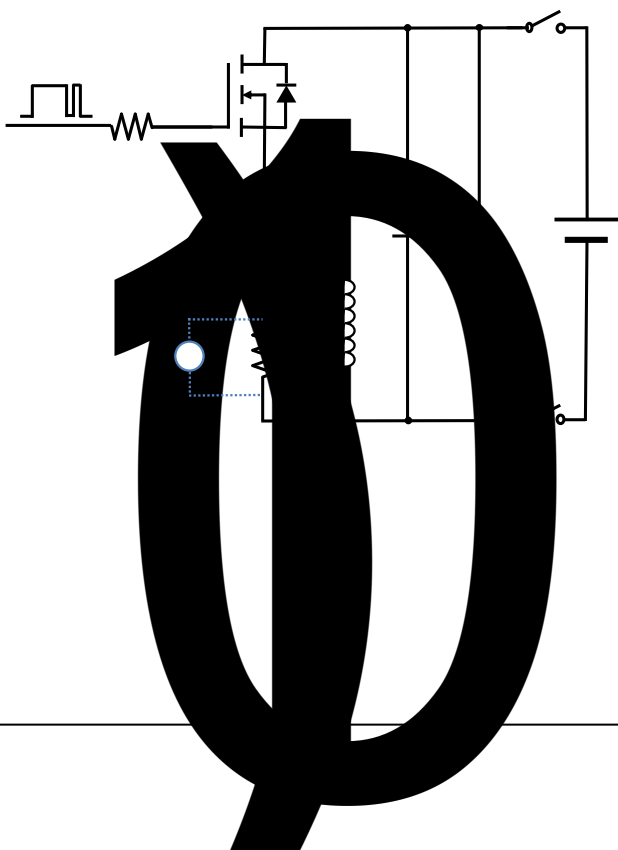
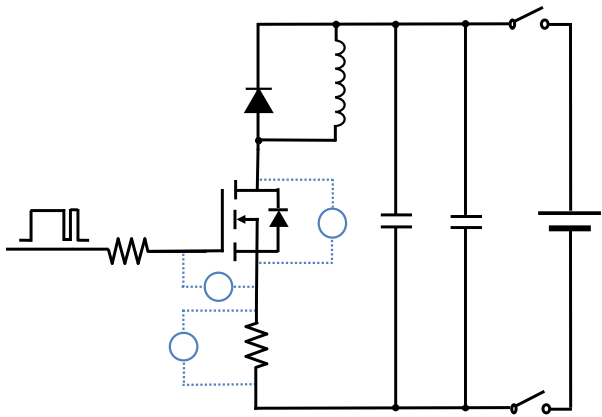
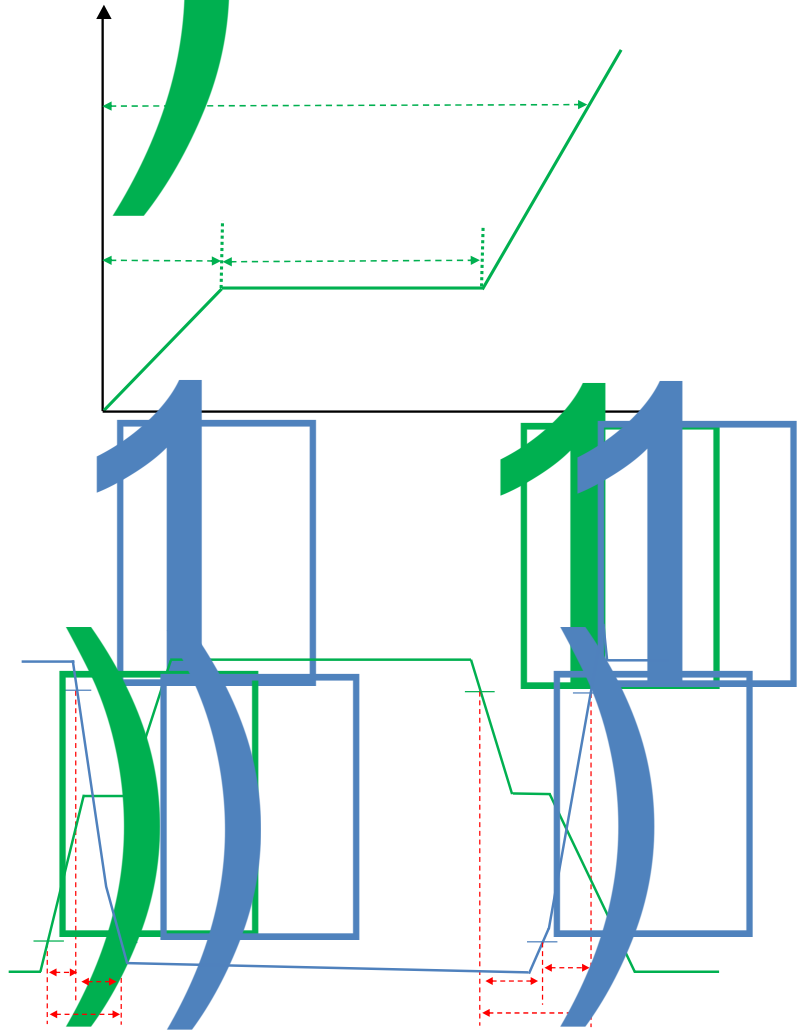
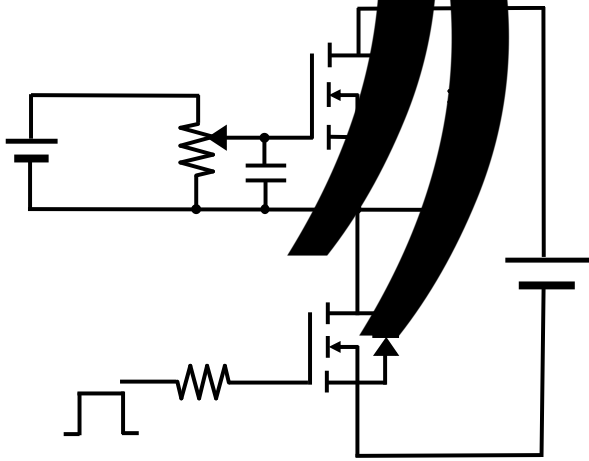


Test Circuit Waveforms





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Disclaimer

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